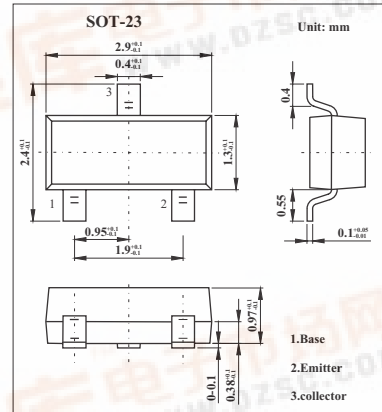


SMD Type Transistors

Silicon NPN Epitaxial Planar Type
2SC2295

■ Features

- Optimum for RF amplification of FM/AM radios.
- High transition frequency f_T .
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	30	V
Collector-emitter voltage	V_{CE0}	20	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	30	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 10\text{ V}, I_E = 0$			0.1	μA
Forward current transfer ratio	h_{FE}	$V_{CB} = 10\text{ V}, I_C = -1\text{ mA}$	70		220	
Transition frequency	f_T	$V_{CB} = 10\text{ V}, I_E = -1\text{ mA}, f = 200\text{ MHz}$	100	250		MHz
Noise figure	NF	$V_{CB} = 10\text{ V}, I_E = -1\text{ mA}, f = 5\text{ MHz}$		2.8	4.0	dB
Reverse transfer impedance	Z_{rb}	$V_{CB} = 10\text{ V}, I_E = -1\text{ mA}, f = 2\text{ MHz}$		22	50	Ω
Reverse transfer capacitance	C_{re}	$V_{CB} = 10\text{ V}, I_C = -1\text{ mA}, f = 10.7\text{ MHz}$		0.9	1.5	pF

■ h_{FE} Classification

Marking	VB	VC
h_{FE}	70~140	110~220